Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Product Summary

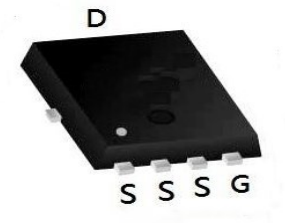
Green

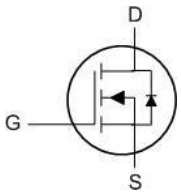
BVDSS	RDSON	ID
60V	12mΩ	30A

Applications

- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

PDFN3333-8L Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	30	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	19	A
I_{DM}	Pulsed Drain Current[2]	141	A
EAS	Single Pulse Avalanche Energy[3]	33.8	mJ
I_{AS}	Avalanche Current	13	A
P_D@T_C=25℃	Total Power Dissipation[4]	27	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	55	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	4.6	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=1A	---	12	15	mΩ
		V_{GS}=4.5V , I_D=1A	---	15	19	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1	1.3	1.8	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=60V, V_{GS}=0V , T_J=100℃	---	---	---	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=20A	---	42	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.2	---	Ω
Q_g	Total Gate Charge	V_{DS}=30V , V_{GS}=10V , I_D=20	---	14	---	nC
Q_{gs}	Gate-Source Charge		---	2.5	---	
Q_{gd}	Gate-Drain Charge		---	2.9	---	
$T_{d(on)}$	Turn-On Delay Time	V_{GS}=10V, V_{DD}=30V, I_D=20A, R_{GEN}=1.6Ω	---	5.7	---	ns
T_r	Rise Time		---	5.1	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14.8	---	
T_f	Fall Time		---	4.6	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , f=1MHz	---	738	---	pF
C_{oss}	Output Capacitance		---	225	---	
C_{rss}	Reverse Transfer Capacitance		---	13.5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	30	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=13A , di/dt=100A/μs , T_J=25℃	---	24	---	nS
Q_{rr}	Reverse Recovery Charge		---	9.6	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
2. The test condition is V_{DD}= 25V, V_{GS}= 10V, L= 0.4mH, I_{AS}= 13A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics

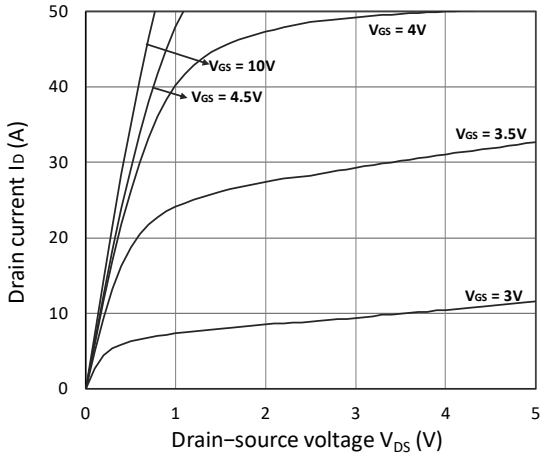


Figure 1. Output Characteristics

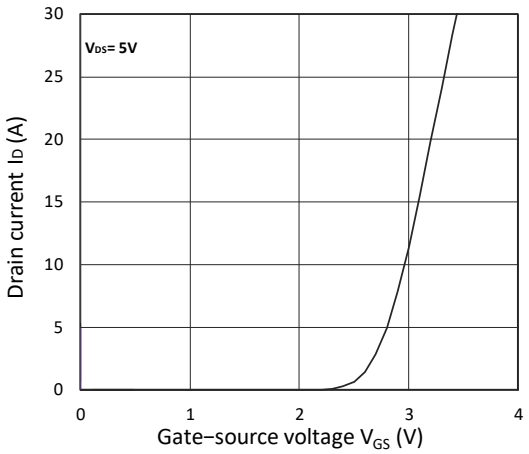


Figure 2. Transfer Characteristics

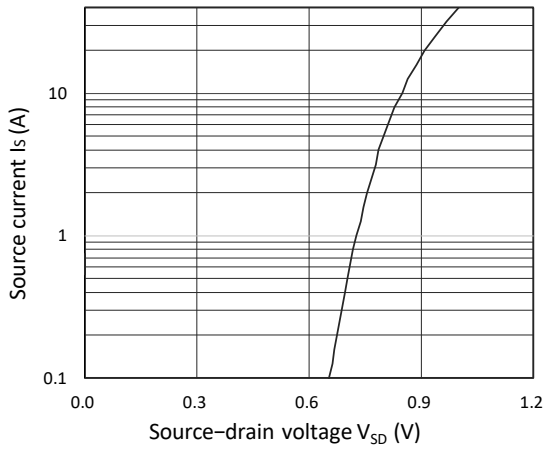


Figure 3. Forward Characteristics of Reverse

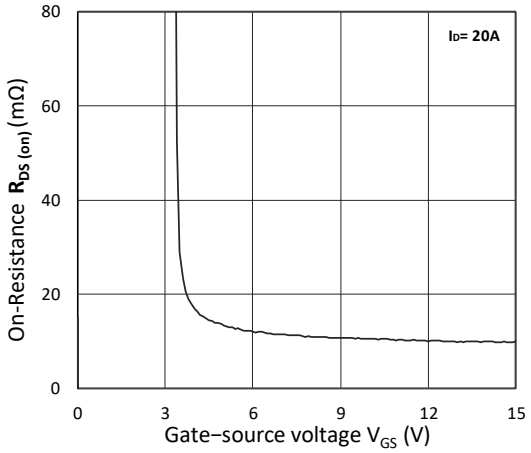


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

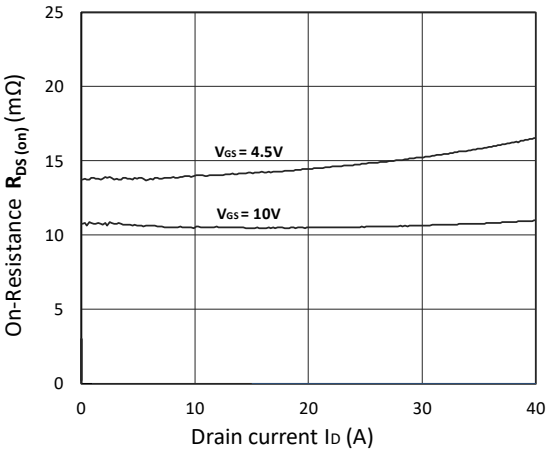


Figure 5. $R_{DS(ON)}$ vs. I_D

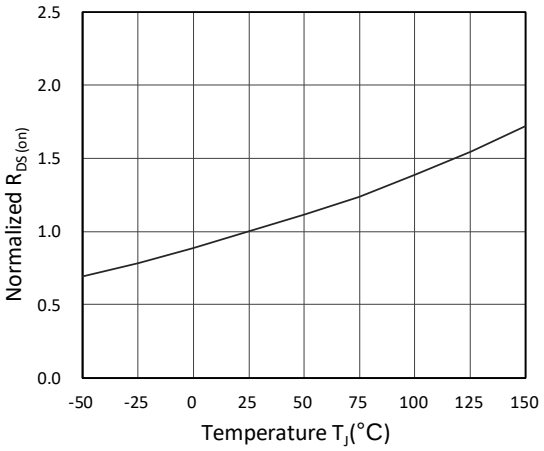


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

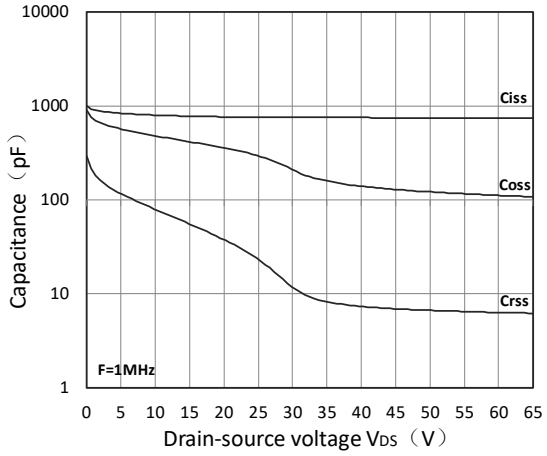


Figure 7. Capacitance Characteristics

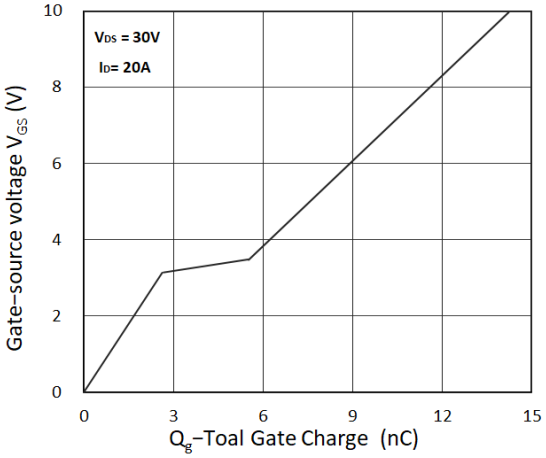


Figure 8. Gate Charge Characteristics

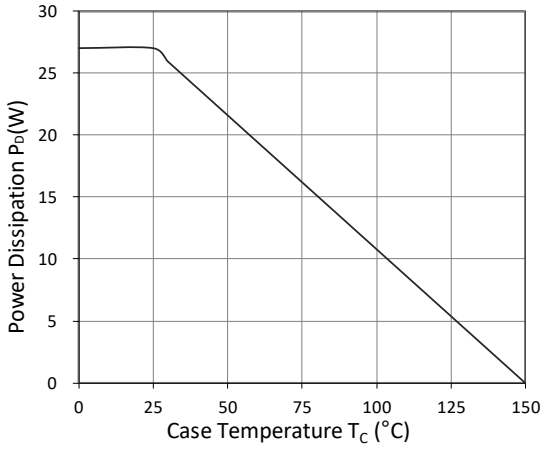


Figure 9. Power Dissipation

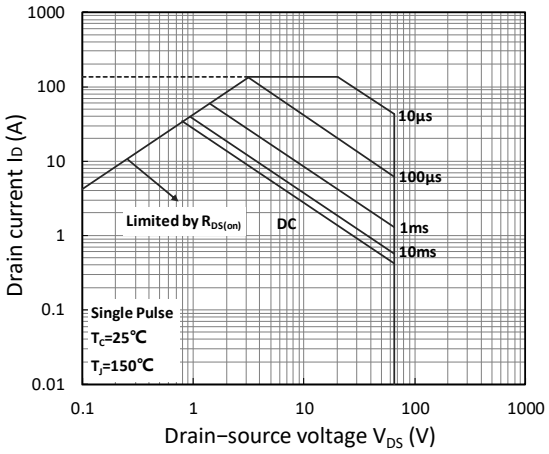


Figure10. Safe Operating Area

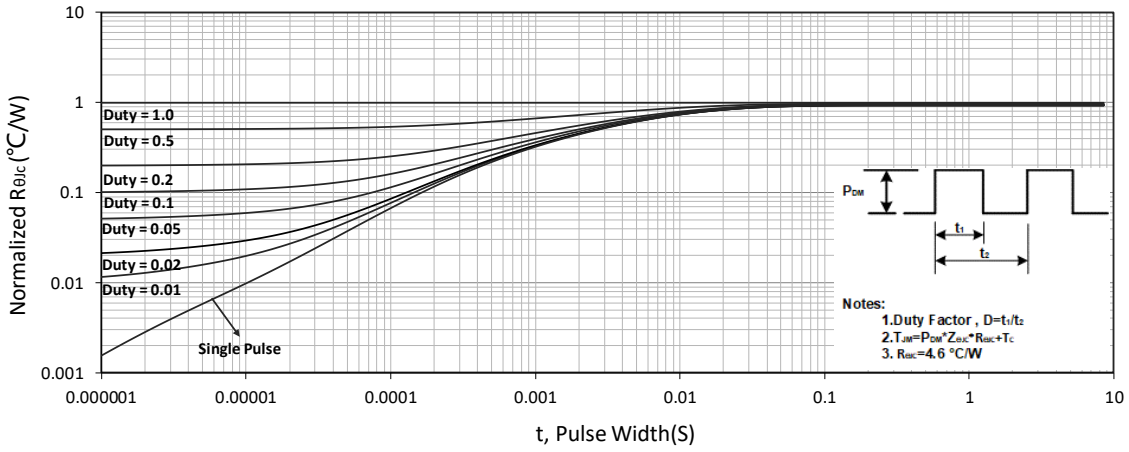
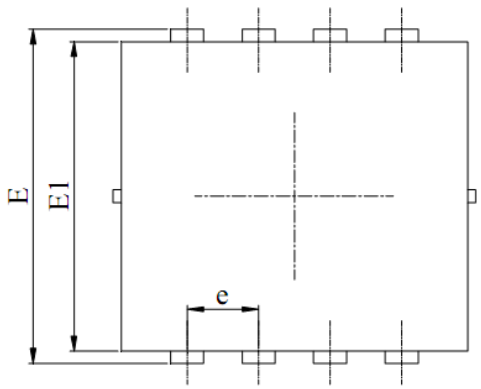
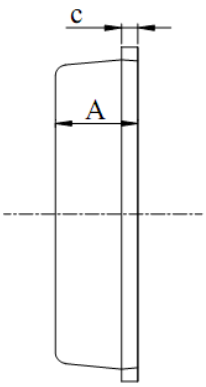


Figure 11. Normalized Maximum Transient Thermal Impedance

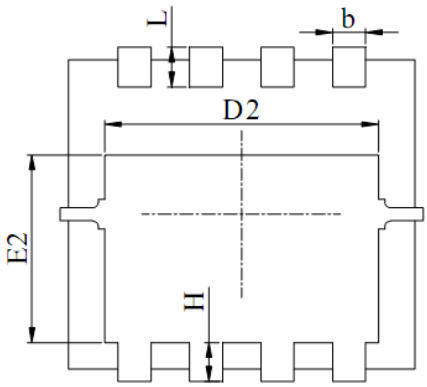
Package Mechanical Data-PDFN3333-8L-Single



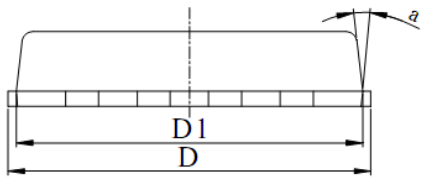
Top View



Side View



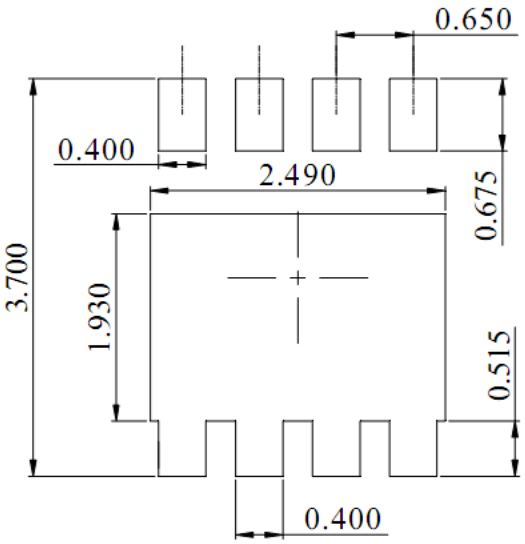
Bottom View



Front View

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS:MILLIMETERS